

LISTING OF THE CLAIMS:

Claims 1-23 (previously withdrawn)

Claim 24. (currently amended) A poly-poly capacitor comprising planar upper and lower plate electrodes, wherein at least the planar upper plate electrode is composed of SiGe polysilicon, said plate electrodes being separated by an insulator structure and said planar upper plate electrode is located directly above said insulator structure and said lower plate electrode is located directly below said insulator structure.

Claim 25. (previously amended) The poly-poly capacitor of Claim 24 wherein the lower plate electrode is composed of polysilicon.

Claim 26. (currently amended) A poly-poly capacitor comprising planar upper and lower plate electrodes, wherein the planar upper plate electrode and the lower plate electrode are both composed of SiGe polysilicon, said plate electrodes being separated by an insulator structure.

Claim 27. (original) The poly-poly capacitor of Claim 24 wherein at least one said plate electrodes is polysilicon from a FET gate or a bipolar emitter.

Claim 28. (original) The poly-poly capacitor of Claim 24 further including a bipolar device region and a FET region, wherein said capacitor, bipolar device region and FET region are electrically isolated from each by isolation regions.

Claim 29. (original) A semiconductor device, comprising:

a capacitor having first and second plate electrodes, one of said plate electrodes being comprised of a first conductive patterned layer; and

a bipolar device having first and second electrodes, one of said electrodes being comprised of said conductive patterned layer;

wherein said first conductive patterned layer is comprised of SiGe material.

Claim 30. (previously amended) A semiconductor structure, comprising

a first layer of polysilicon patterned to form a first electrode of a MOS device and a first plate electrode of a capacitor, and

a second layer of polysilicon patterned to form a first electrode of a bipolar device and a second plate electrode of said capacitor, said second layer being comprised of SiGe polysilicon.

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